

NPN SILICON RF TRANSISTOR

DESCRIPTION:

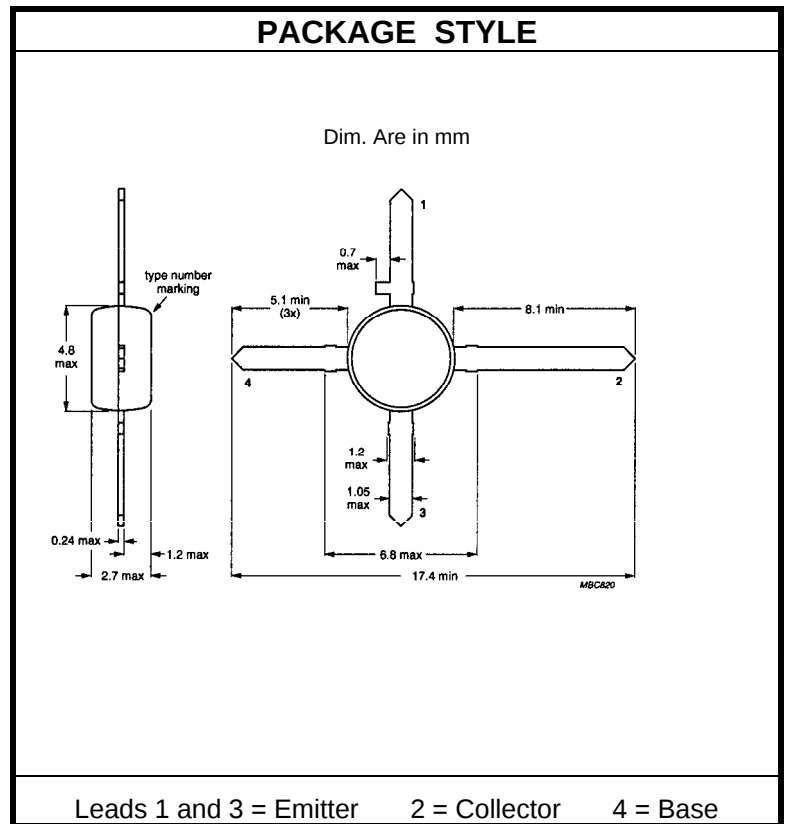
The **ASI MRF901** is Designed for high gain. Low noise small-signal amplifiers. Applications up to 2.5 GHz.

FEATURES:

- Low Noise Figure
- High Gain
- **Common Emitter**

MAXIMUM RATINGS

I_C	30 mA
V_{CBO}	25 V
V_{CEO}	15 V
V_{EBO}	2.0 V
P_{DISS}	0.375 W @ $T_C = 75^\circ\text{C}$
T_J	-55°C to $+150^\circ\text{C}$
T_{STG}	-55°C to $+150^\circ\text{C}$
θ_{JC}	200 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 0.1\text{ mA}$			25			V
BV_{CEO}	$I_C = 1.0\text{ mA}$			15			V
BV_{EBO}	$I_E = 0.1\text{ mA}$			2.0			V
I_{CBO}	$V_{CB} = 15\text{ V}$					50	nA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 5.0\text{ mA}$		30	80	200	---
C_{cb}	$V_{CB} = 10\text{ V}$	$f = 1.0\text{ MHz}$			0.40	1.0	pF
f_T	$V_{CE} = 10\text{ V}$	$I_C = 15\text{ mA}$	$f = 1.0\text{ GHz}$		4.5		GHz
NF_{MIN}	$V_{CE} = 6.0\text{ V}$	$I_C = 15\text{ mA}$	$f = 1.0\text{ GHz}$		2.0	2.5	dB